

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
30	0.003 at $V_{GS} = 10$ V	25
	0.004 at $V_{GS} = 4.5$ V	22

FEATURES

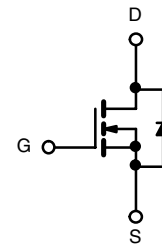
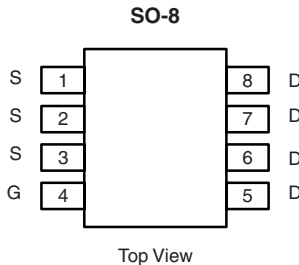
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Gen II
- Ultra Low On-Resistance Using High Density TrenchFET Power MOSFET Technology



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Synchronous Buck Low-Side
 - Notebook
 - Server
 - Workstation
- Synchronous Rectifier-POL



N-Channel MOSFET

Ordering Information: Si4320DY-T1-E3 (Lead (Pb)-free)
Si4320DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}	30		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	25	17	A
		$T_A = 70$ °C	20	13	
Pulsed Drain Current (10 μ s Pulse Width)	I_{DM}	70			
Continuous Source Current (Diode Conduction) ^a	I_S	2.9	1.3		
Avalanche Current	I_{AS}	50		W	
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	3.5		1.6
		$T_A = 70$ °C	2.2	1	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ s	R_{thJA}	29	35	°C/W
	Steady State		67	80	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	13	16	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

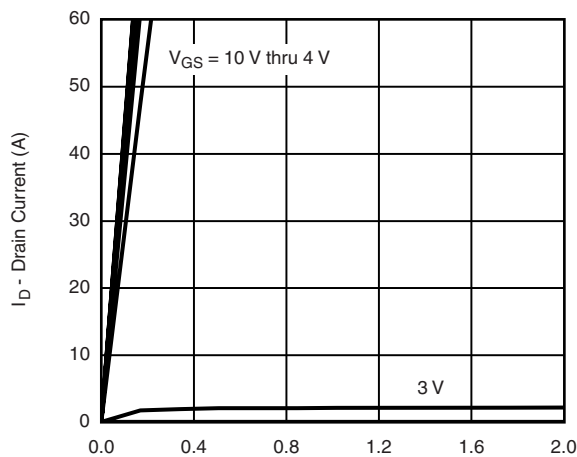
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		3.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$		0.0024	0.003	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 22\text{ A}$		0.0032	0.004	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 25\text{ A}$		110		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.9\text{ A}, V_{GS} = 0\text{ V}$		0.72	1.1	V
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		6500		μF
Output Capacitance	C_{oss}			930		
Reverse Transfer Capacitance	C_{rss}			610		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		45	70	nC
Gate-Source Charge	Q_{gs}			20		
Gate-Drain Charge	Q_{gd}			16		
Gate Resistance	R_g	$f = 1.0\text{ MHz}$		1.1		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		27	40	ns
Rise Time	t_r			21	35	
Turn-Off Delay Time	$t_{d(off)}$			107	160	
Fall Time	t_f			43	65	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.9\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		45	70	

Notes:

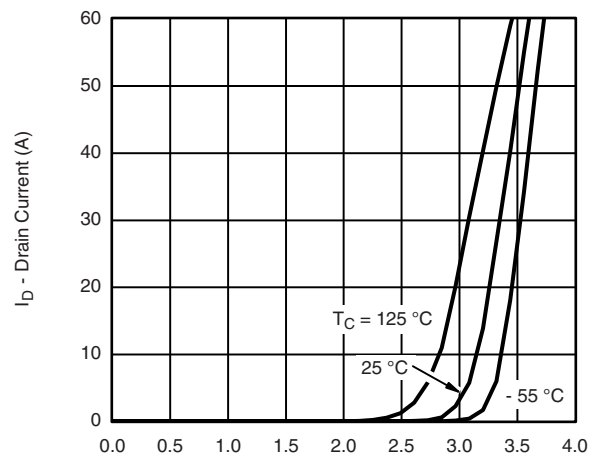
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted

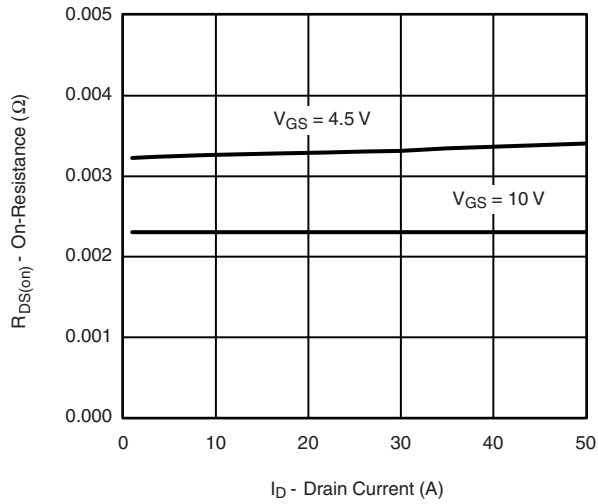


Output Characteristics

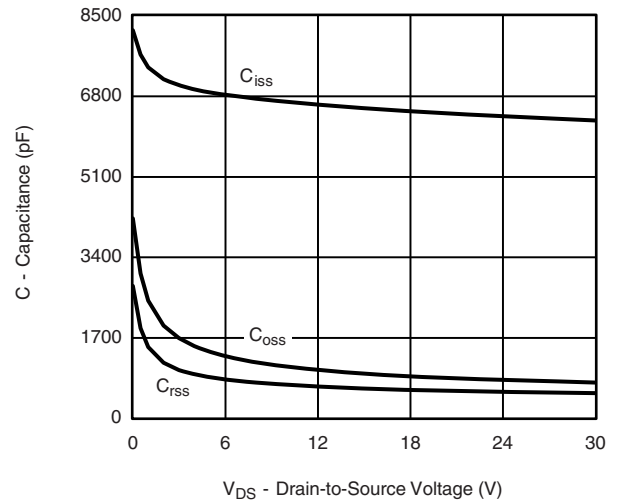


Transfer Characteristics

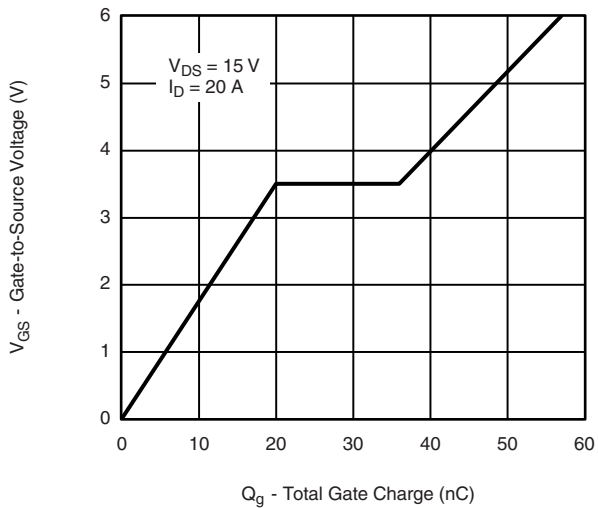
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



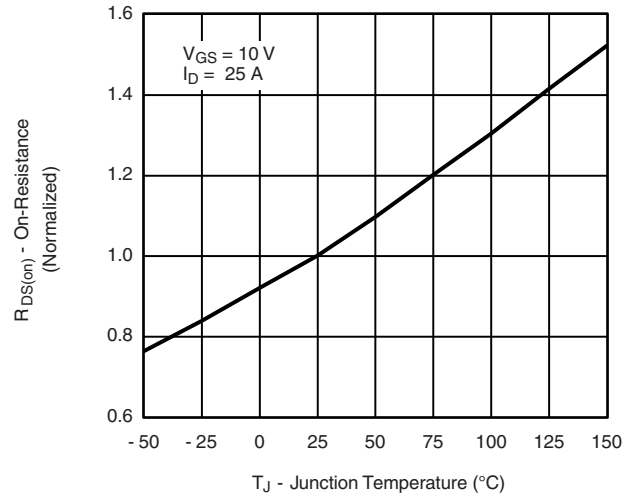
On-Resistance vs. Drain Current



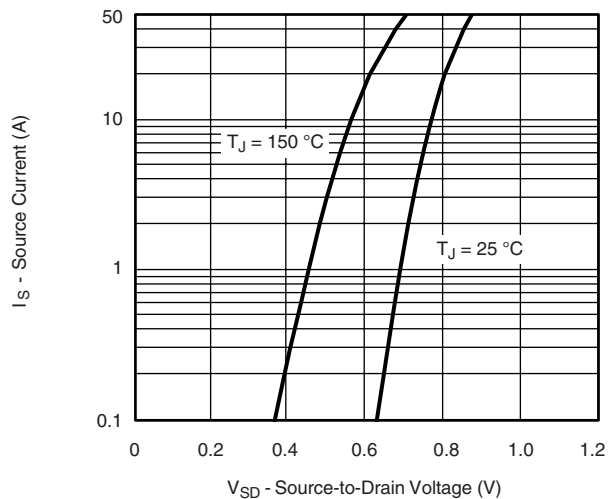
Capacitance



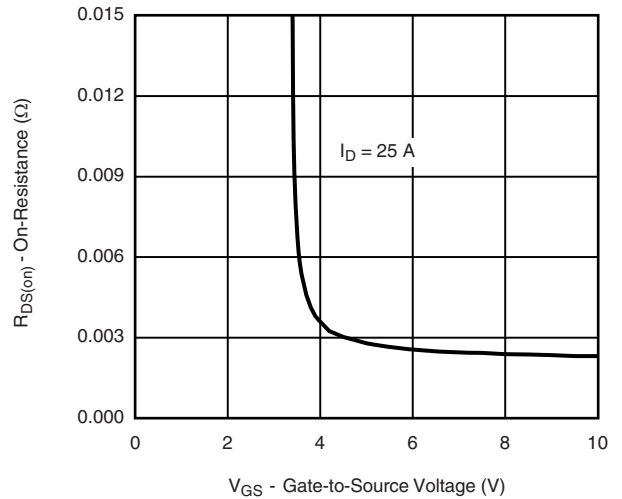
Gate Charge



On-Resistance vs. Junction Temperature

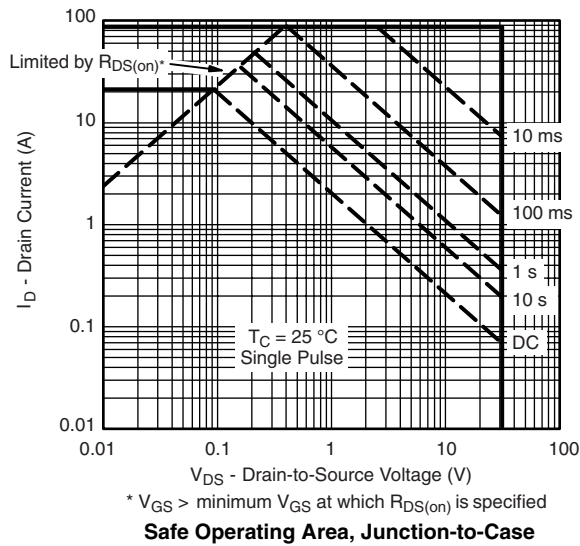
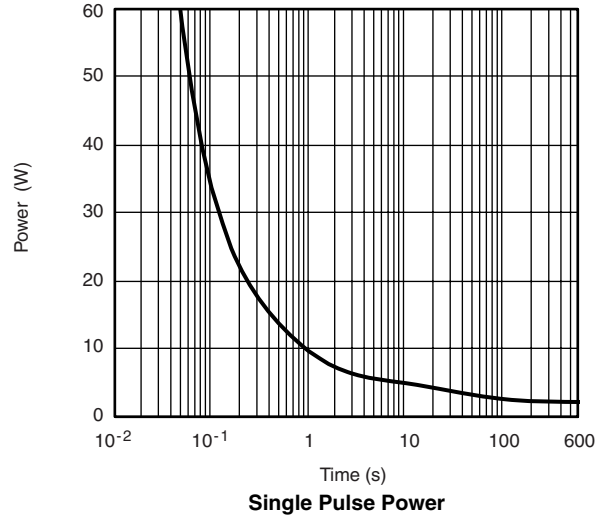
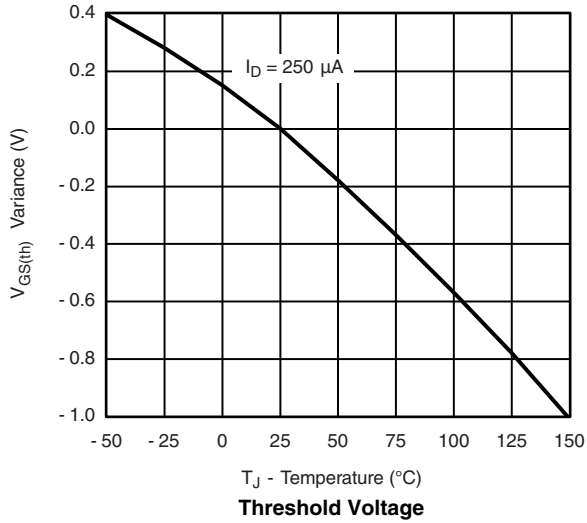


Source-Drain Diode Forward Voltage



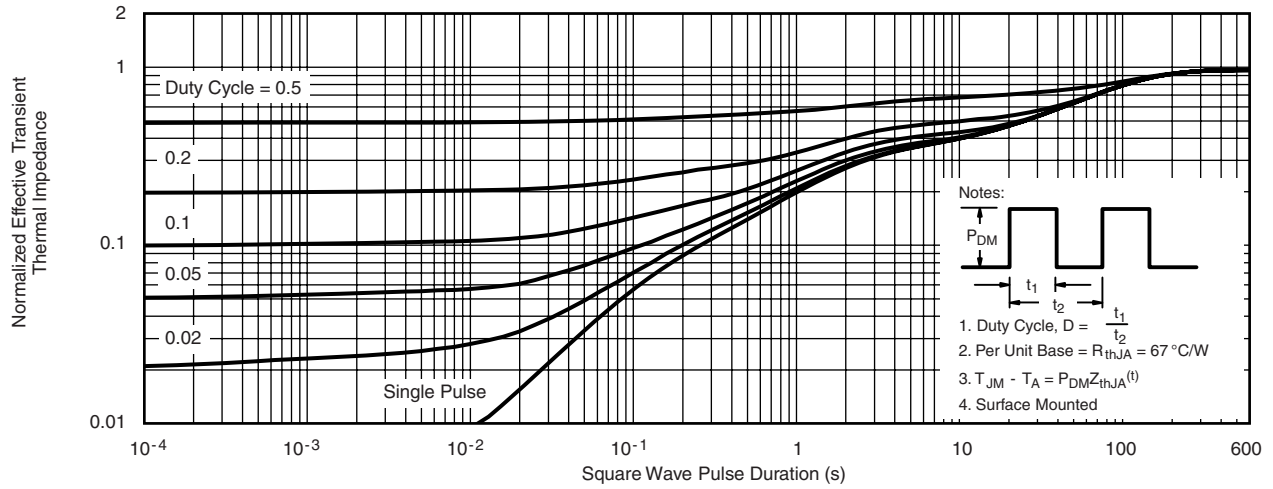
On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

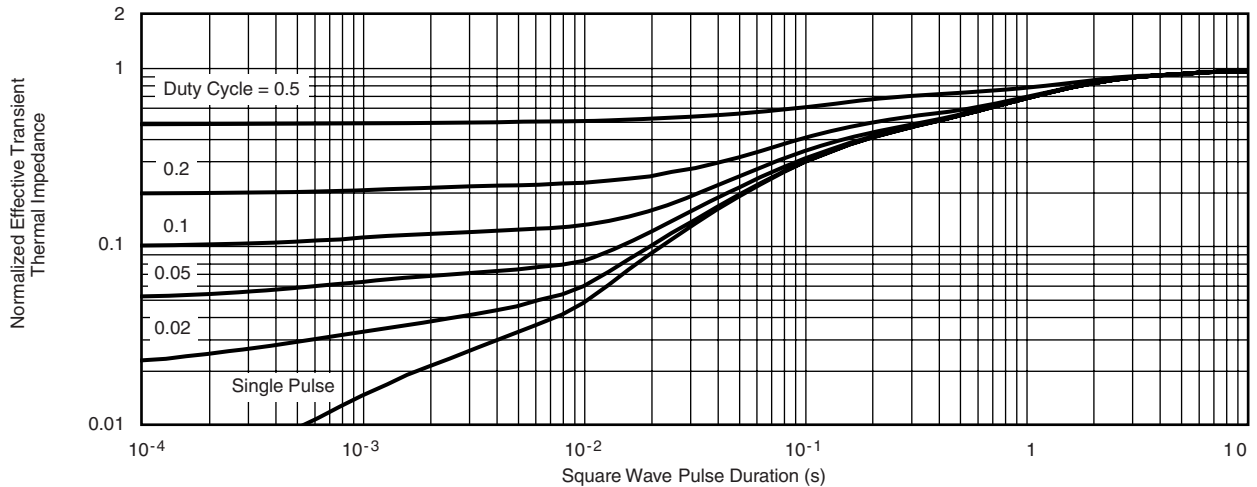




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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